

ABSTRACT OF THE DISCLOSURE

A plasma treatment apparatus and a method for plasma treatment are provided that made possible to control accurately a distance between plasma and an object to
5 be treated (hereinafter referred to as an object), and that facilitated a transportation of a substrate that a width is thin and grown in size. The plasma treatment apparatus of the present invention is provided with a gas supply means for introducing a processing gas into a place between a first electrode and a second electrode under an atmospheric pressure or around atmospheric pressure; a plasma
10 generation means for generating plasma by applying a high frequency voltage to the first electrode or the second electrode under the condition that the processing gas is introduced; and, a transport means for transporting the object by floating the object by blowing the processing gas or a transporting gas to the object. An etching treatment; an ashing treatment; a thin film formation; or a cleaning treatment of
15 components using the first electrode and the second electrode is carried out by moving a relative position between the first electrode and the second electrode, and the object.